Ordering number : ENN8180

SANYO Semiconductors
DATA SHEET

N-Channel Silicon MOSFET

CPH5612 — General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.
- Composite type with 2 MOSFETs contained in a single package, facilitaing-density mounting.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		100	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		1	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	4	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (600mm²×0.8mm) 1unit	0.9	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		–55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	100			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS}(off)$	V_{DS}=10V, I_D=1mA	0.4		1.3	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=10V, I_D=500mA	1.8	2.6		S
Static Drain-to-Source On-State Resistance	$R_{DS}(on)1$	I_D=500mA, V_{GS}=4V		430	570	mΩ
	$R_{DS}(on)2$	I_D=500mA, V_{GS}=2.5V		450	650	mΩ
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		350		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		20		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		12		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		15		ns
Rise Time	t_r	See specified Test Circuit.		11		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		54		ns
Fall Time	t_f	See specified Test Circuit.		30		ns

Marking : FS

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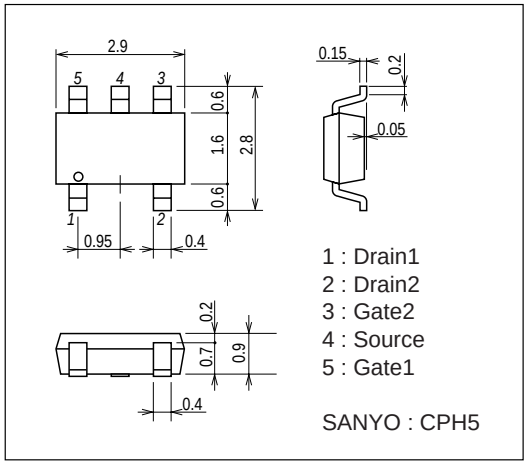
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V_{DS}=50V, V_{GS}=4V, I_D=1A		4.4		nC
Gate-to-Source Charge	Qgs	V_{DS}=50V, V_{GS}=4V, I_D=1A		1.2		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=50V, V_{GS}=4V, I_D=1A		0.8		nC
Diode Forward Voltage	V_{SD}	I_S=1A, V_{GS}=0		0.82	1.2	V

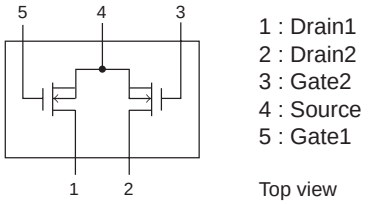
Package Dimensions

unit : mm

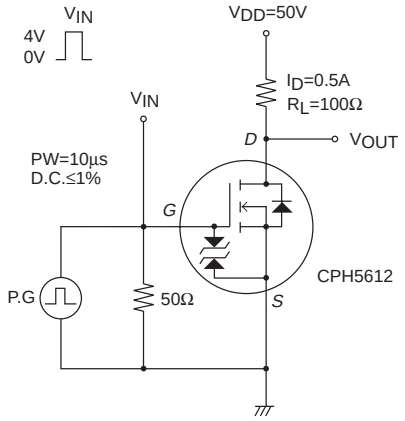
2168

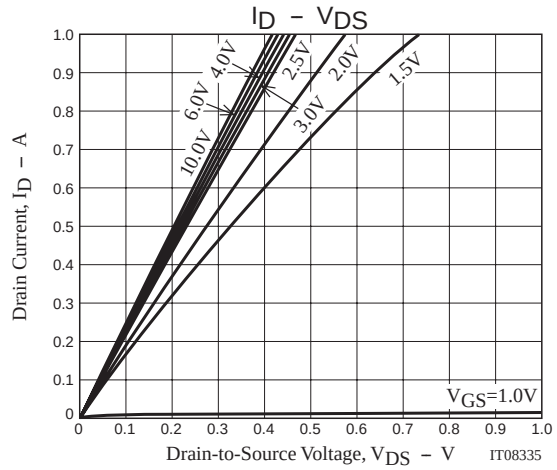


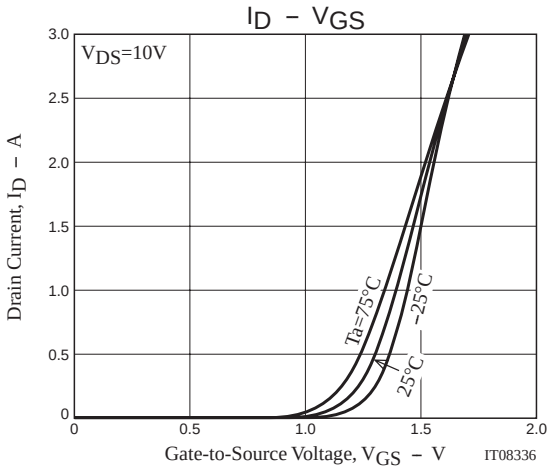
Electrical Connection

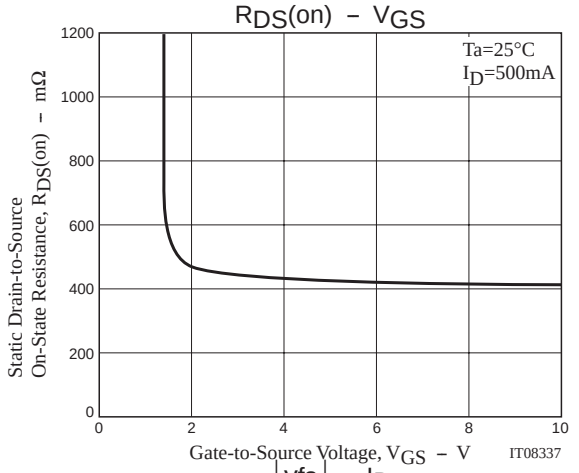


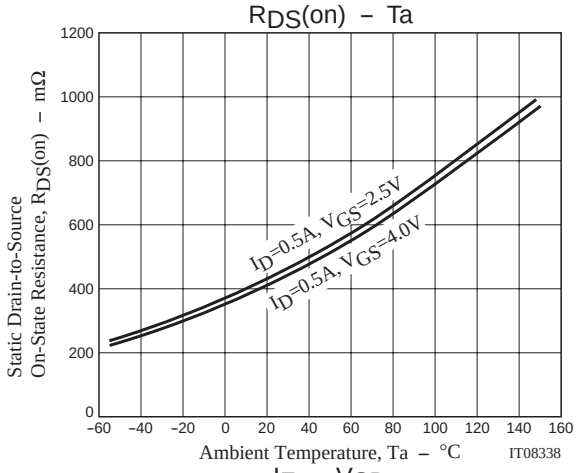
Switching Time Test Circuit

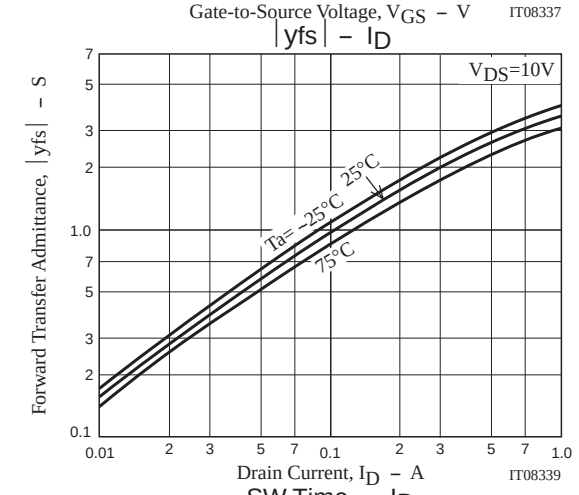


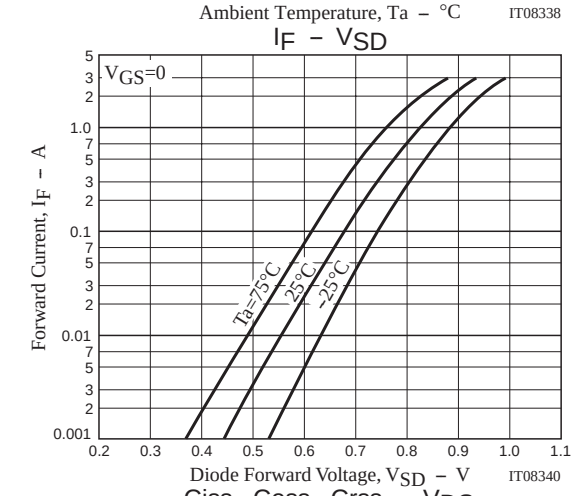


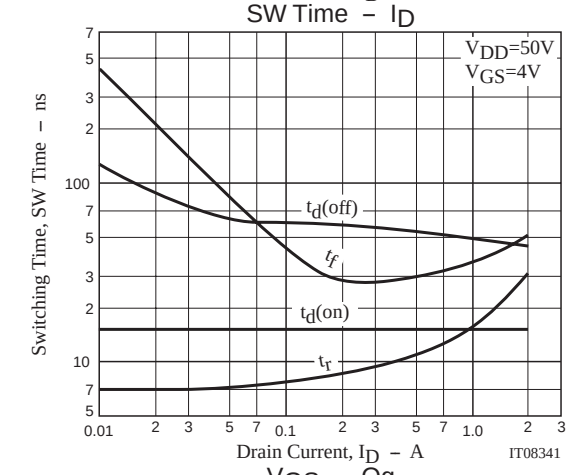


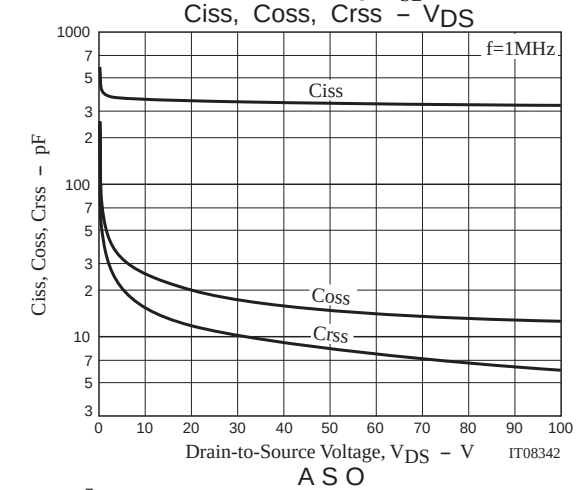


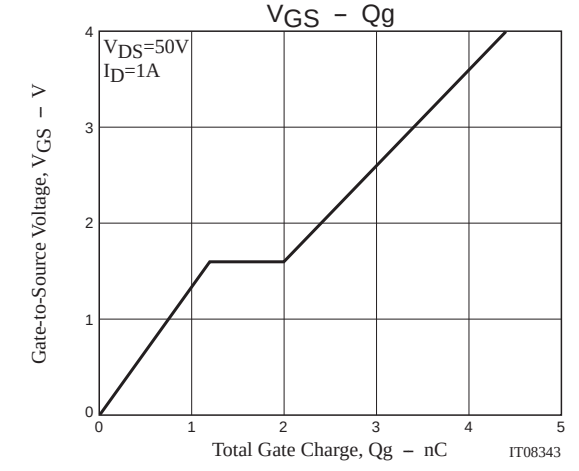


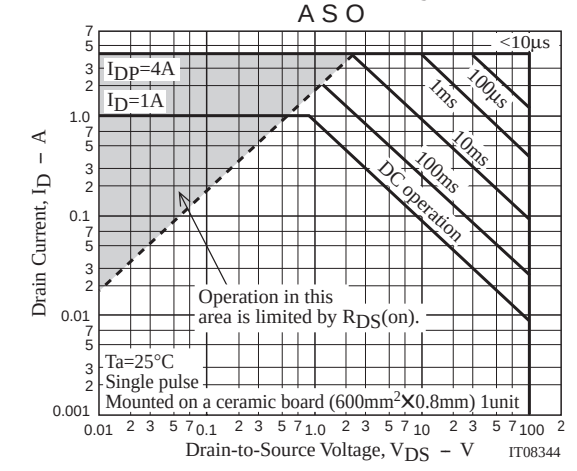


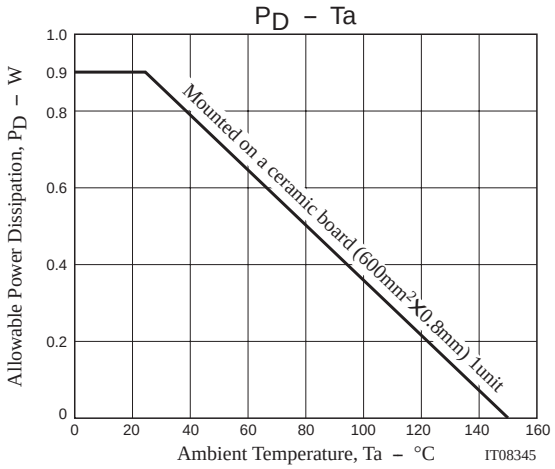












Note on usage : Since the CPH5612 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.